

High performance SBD series with fine diffusion process 1 to 5A general Schottky Barrier Diode

Overview

This product is the JBS ※ structure Schottky Barrier Diode with the leading-edge process technology, and features Low V_F / I_R characteristics in small packages.

※Junction Barrier Schottky

Feature

- Low V_F
- Low I_R
- Small packages

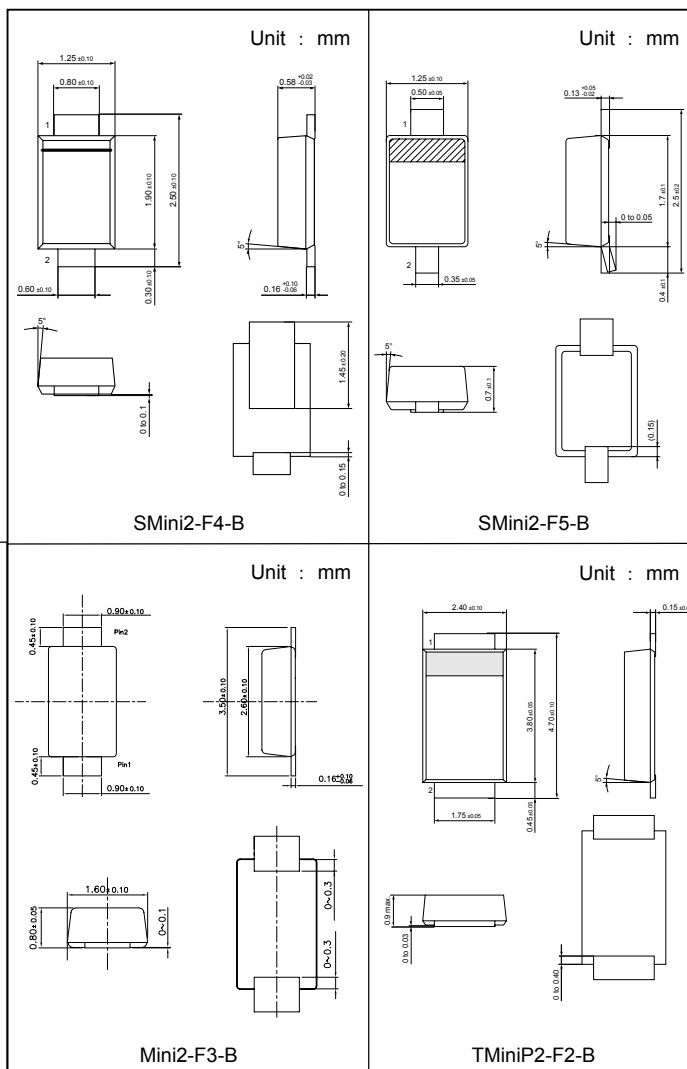
Applications

For rectification
For reverse current prevention

Lineup

• Electrical Characteristics ($T_a=25^\circ\text{C}$)

Part number	I_F (A)	V_R (V)	$V_{Fmax.}(@I_F)$ (V)	$I_{Rmax.}(@V_R)$ (μA)	Package
DB2J317	1.0	30	0.52	100	SMini2-F5-B
DB2J411		40	0.58	100	SMini2-F5-B
DB21413	2.0	40	0.53	150	SMini2-F4-B
DB2W319	3.0	30	0.49	200	Mini2-F3-B
DB2X415		40	0.55	200	Mini2-F4-B
DB24417	5.0	40	0.54	300	TMiniP2-F2-B



Products and specifications are subject to change without notice. Please ask for the latest Product Standards to guarantee the satisfaction of your product requirements.

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